



SPP9435B

P-Channel Enhancement Mode MOSFET

DESCRIPTION

The SPP9435B is the P-Channel logic enhancement mode power field effect transistors are produced using high cell density , DMOS trench technology.

This high density process is especially tailored to minimize on-state resistance.

These devices are particularly suited for low voltage application , notebook computer power management and other battery powered circuits where high-side switching .

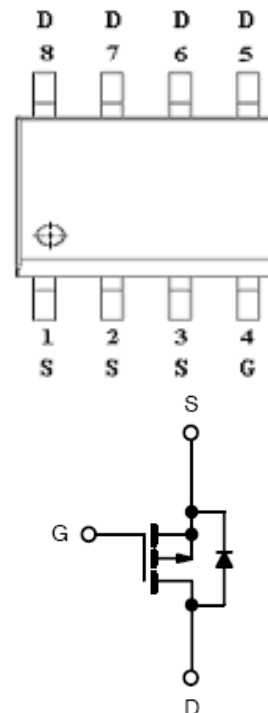
FEATURES

- ◆ -30V/-7.2A, $R_{DS(ON)}=65m\Omega@V_{GS}=-10V$
- ◆ -30V/-5.0A, $R_{DS(ON)}=90m\Omega@V_{GS}=-4.5V$
- ◆ Super high density cell design for extremely low $R_{DS(ON)}$
- ◆ Exceptional on-resistance and maximum DC current capability
- ◆ SOP – 8P package design

APPLICATIONS

- Power Management in Note book
- Portable Equipment
- Battery Powered System
- DC/DC Converter
- Load Switch
- DSC
- LCD Display inverter

PIN CONFIGURATION(SOP – 8P)



PART MARKING





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PIN DESCRIPTION

| Pin | Symbol | Description |
|-----|--------|-------------|
| 1 | S | Source |
| 2 | S | Source |
| 3 | S | Source |
| 4 | G | Gate |
| 5 | D | Drain |
| 6 | D | Drain |
| 7 | D | Drain |
| 8 | D | Drain |

ORDERING INFORMATION

| Part Number | Package | Part Marking |
|---------------|---------|--------------|
| SPP9435BS8RGB | SOP- 8P | SPP9435B |

※ SPP9435BS8RGB 13" Tape Reel ; Pb – Free ; Halogen – Free

ABSOLUTE MAXIMUM RATINGS

(TA=25°C Unless otherwise noted)

| Parameter | Symbol | Typical | Unit |
|---|------------------|---------|------|
| Drain-Source Voltage | V _{DSS} | -30 | V |
| Gate –Source Voltage | V _{GSS} | ±20 | V |
| Continuous Drain Current(T _J =150°C) | I _D | TA=25°C | -7.2 |
| | | TA=70°C | -5.0 |
| Pulsed Drain Current | I _{DM} | -25 | A |
| Continuous Source Current(Diode Conduction) | I _S | -2.3 | A |
| Power Dissipation | P _D | TA=25°C | 2.8 |
| | | TA=70°C | 1.8 |
| Operating Junction Temperature | T _J | -55/150 | °C |
| Storage Temperature Range | T _{STG} | -55/150 | °C |
| Thermal Resistance-Junction to Ambient | R _{θJA} | 70 | °C/W |



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ELECTRICAL CHARACTERISTICS

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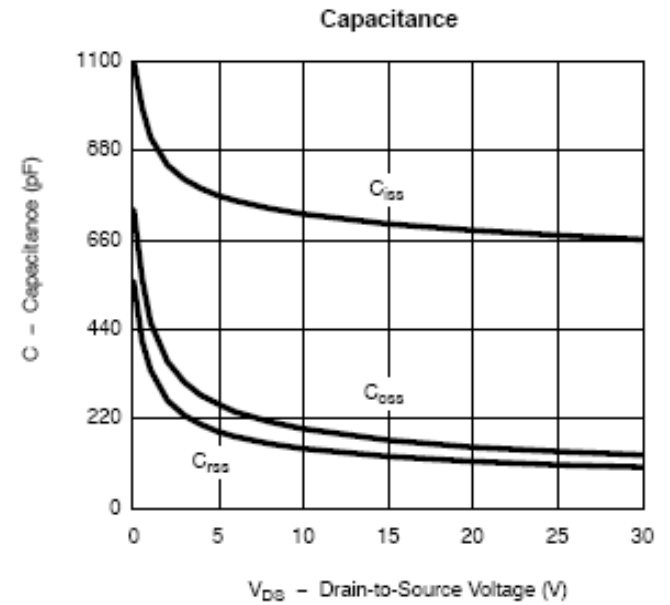
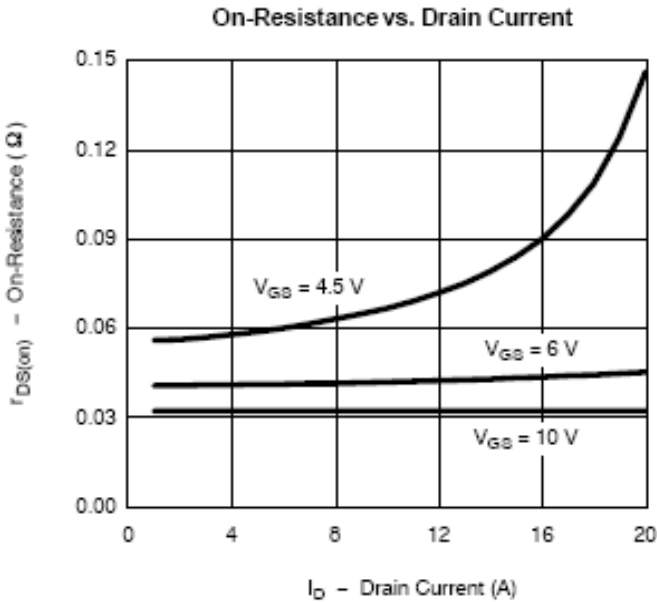
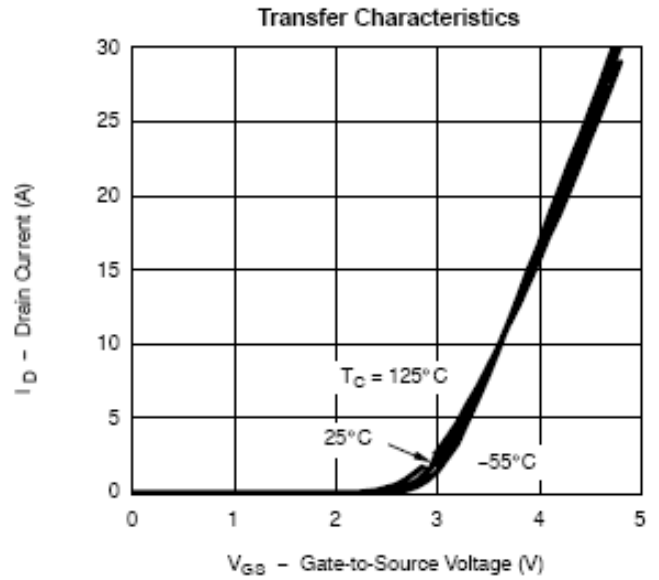
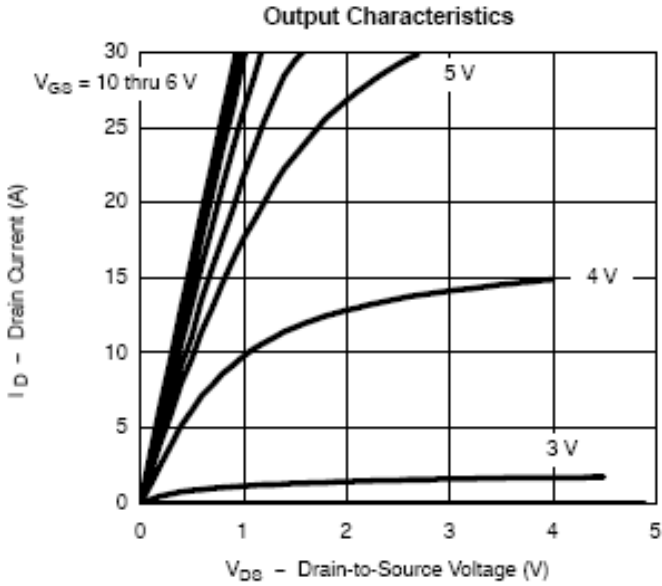
| Parameter | Symbol | Conditions | Min. | Typ | Max. | Unit |
|---------------------------------|---------------|---|------|-------|-----------|----------|
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS}=0V, I_D=-250\mu A$ | -30 | | | V |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=-250\mu A$ | -0.8 | | -2.5 | |
| Gate Leakage Current | I_{GSS} | $V_{DS}=0V, V_{GS}=\pm 20V$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=-24V, V_{GS}=0V$ | | | -1 | uA |
| | | $V_{DS}=-24V, V_{GS}=0V$ $T_J=55^\circ C$ | | | -5 | |
| On-State Drain Current | $I_{D(on)}$ | $V_{DS}=-5V, V_{GS}=-4.5V$ | -10 | | | A |
| Drain-Source On-Resistance | $R_{DS(on)}$ | $V_{GS}=-10V, I_D=-7.2A$ | | 0.057 | 0.065 | Ω |
| | | $V_{GS}=-4.5V, I_D=-5.0A$ | | 0.083 | 0.090 | |
| Forward Transconductance | g_{fs} | $V_{DS}=-15V, I_D=-5.7A$ | | 13 | | S |
| Diode Forward Voltage | V_{SD} | $I_S=-1.3A, V_{GS}=0V$ | | -0.55 | -1.0 | V |
| Dynamic | | | | | | |
| Total Gate Charge | Q_g | $V_{DS}=-15V, V_{GS}=-10V$ $I_D=-3.5A$ | | 10 | 18 | nC |
| Gate-Source Charge | Q_{gs} | | | 1.6 | | |
| Gate-Drain Charge | Q_{gd} | | | 3.0 | | |
| Input Capacitance | C_{iss} | $V_{DS}=-15V, V_{GS}=0V$ $f=1MHz$ | | 450 | | pF |
| Output Capacitance | C_{oss} | | | 95 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 55 | | |
| Turn-On Time | $t_{d(on)}$ | $V_{DD}=-15V, R_L=15\Omega$ $I_D=-1.0A, V_{GEN}=-10V$ $R_G=6\Omega$ | | 8 | 18 | nS |
| | t_r | | | 8 | 18 | |
| Turn-Off Time | $t_{d(off)}$ | | | 25 | 50 | |
| | t_f | | | 25 | 35 | |



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TYPICAL CHARACTERISTICS

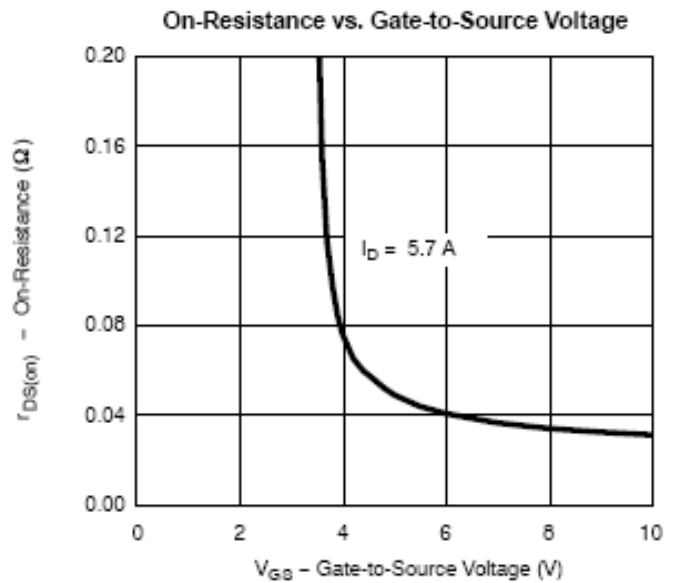
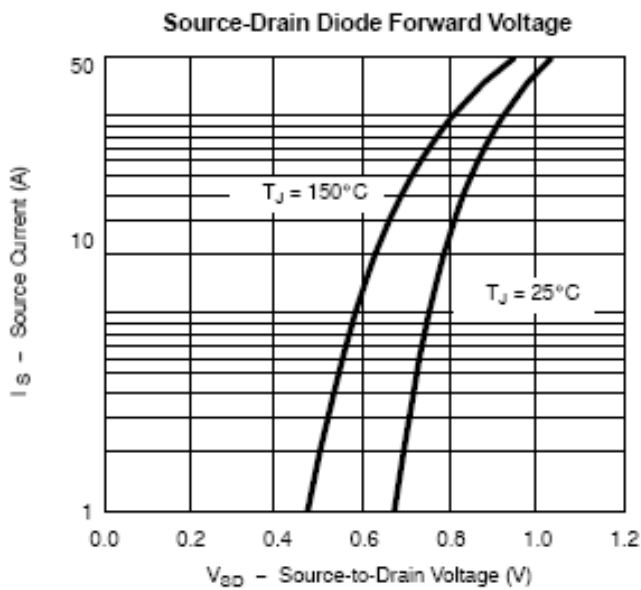
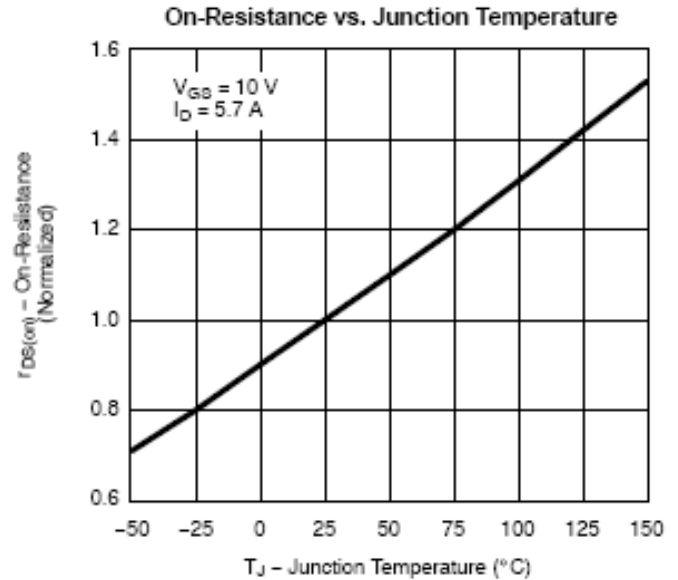
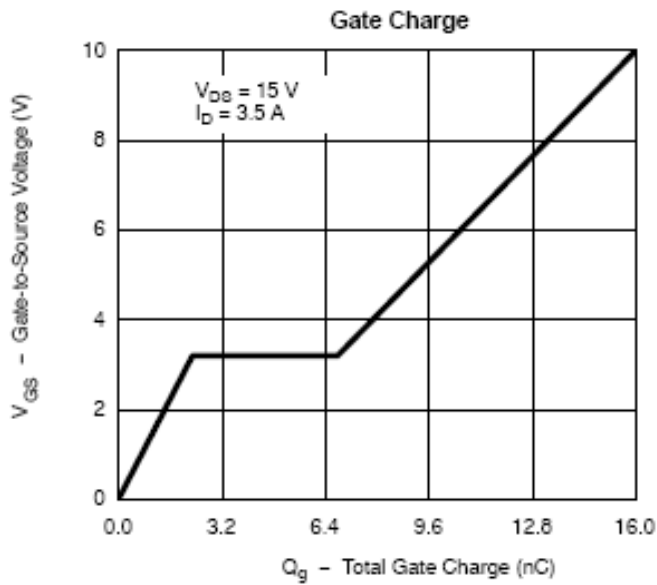




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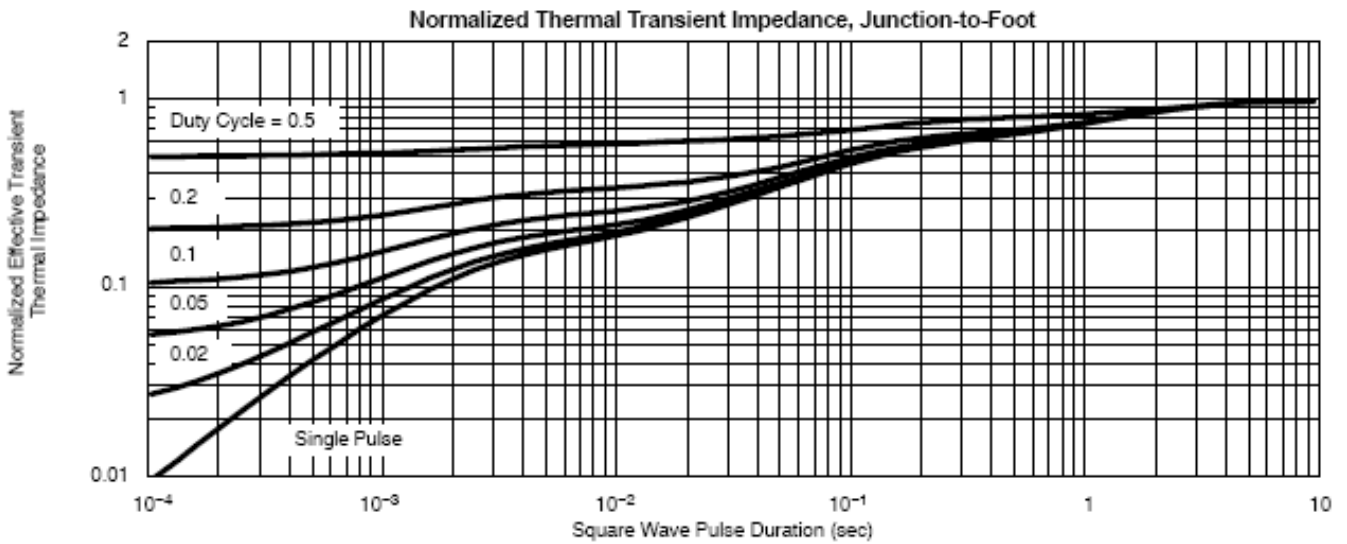
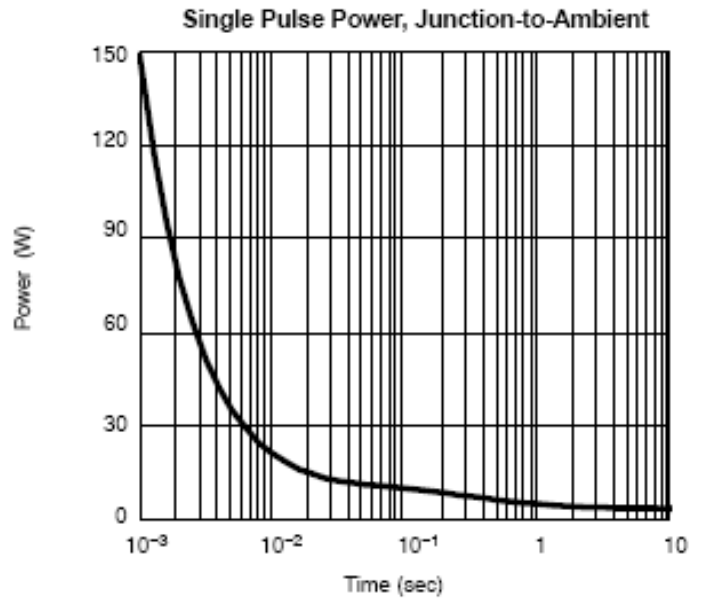
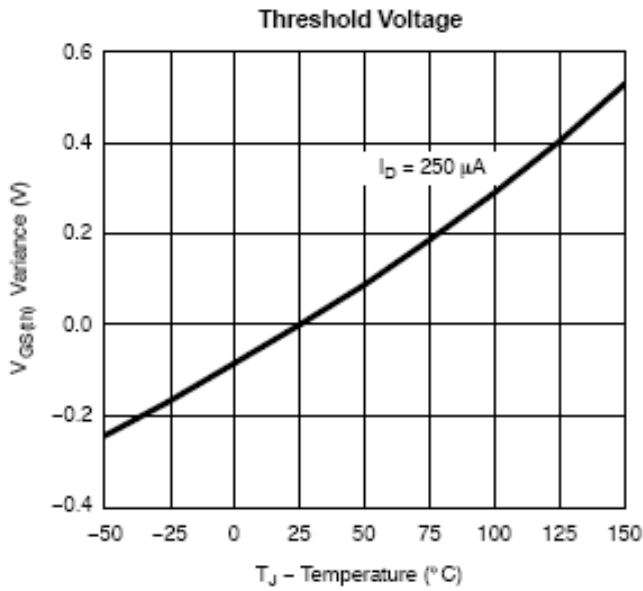




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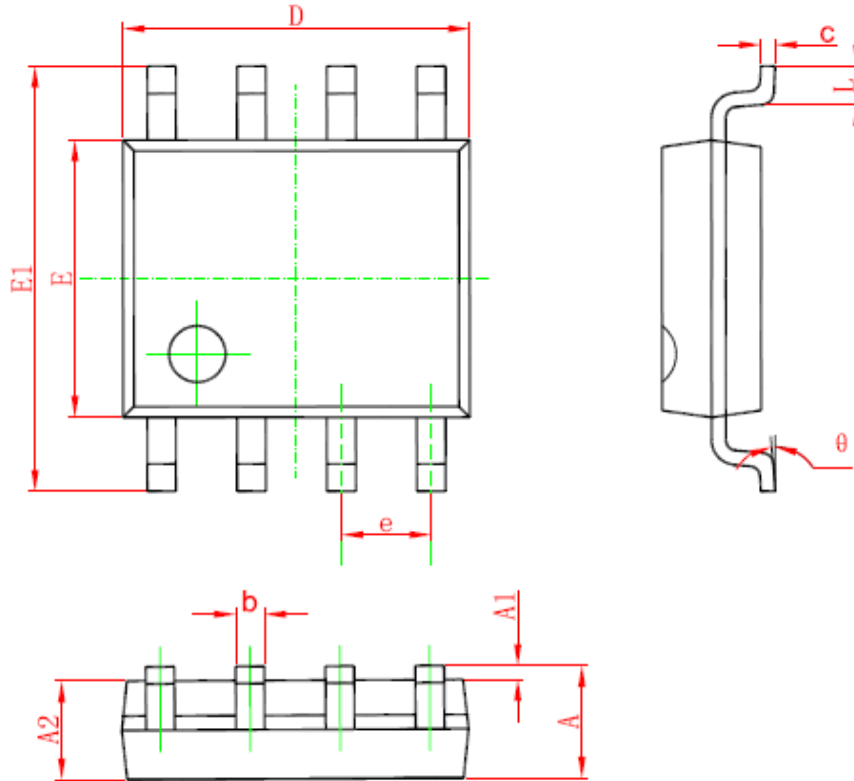




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SOP-8 PACKAGE OUTLINE



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|-------|----------------------|-------|
| | Min | Max | Min | Max |
| A | 1.350 | 1.750 | 0.053 | 0.069 |
| A1 | 0.100 | 0.250 | 0.004 | 0.010 |
| A2 | 1.350 | 1.550 | 0.053 | 0.061 |
| b | 0.330 | 0.510 | 0.013 | 0.020 |
| c | 0.170 | 0.250 | 0.006 | 0.010 |
| D | 4.700 | 5.100 | 0.185 | 0.200 |
| E | 3.800 | 4.000 | 0.150 | 0.157 |
| E1 | 5.800 | 6.200 | 0.228 | 0.244 |
| e | 1.270 (BSC) | | 0.050 (BSC) | |
| L | 0.400 | 1.270 | 0.016 | 0.050 |
| θ | 0° | 8° | 0° | 8° |



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